

XP133A1235SR



Power MOSFET

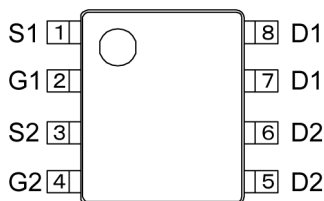
- ◆ N-Channel Power MOSFET
- ◆ DMOS Structure
- ◆ Low On-State Resistance : 0.035 Ω (MAX.)
- ◆ Ultra High-Speed Switching
- ◆ SOP-8 Package
- ◆ Two FET Devices Built-in

■ GENERAL DESCRIPTION

The XP133A1235SR is an N-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics. Two FET devices are built into the one package. Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

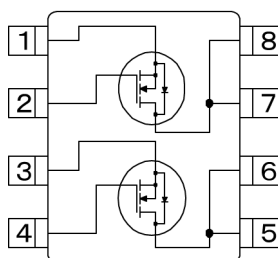
The small SOP-8 package makes high density mounting possible.

■ PIN CONFIGURATION



SOP-8
(TOP VIEW)

■ EQUIVALENT CIRCUIT



N-channel MOSFET
(2 FET devices built-in)

■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

■ FEATURES

Low On-State Resistance : $R_{ds(on)}=0.035\ \Omega$ ($V_{gs}=4.5V$)
: $R_{ds(on)}=0.048\ \Omega$ ($V_{gs}=2.5V$)

Ultra High-Speed Switching

Driving Voltage : 2.5V

High Density Mounting : SOP-8

■ PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1	S1	Source
2	G1	Gate
3	S2	Source
4	G2	Gate
5~6	D2	Drain
7~8	D1	Drain

■ ABSOLUTE MAXIMUM RATINGS

$T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V_{dss}	20	V
Gate-Source Voltage	V_{gss}	± 12	V
Drain Current (DC)	I_d	6	A
Drain Current (Pulse)	I_{dp}	20	A
Reverse Drain Current	I_{dr}	6	A
Channel Power Dissipation *	P_d	2	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

* When implemented on a glass epoxy PCB

■ ELECTRICAL CHARACTERISTICS

DC Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	I _{dss}	V _{ds} =20V, V _{gs} =0V	-	-	10	μA
Gate-Source Leak Current	I _{gss}	V _{gs} =±12V, V _{ds} =0V	-	-	±1	μA
Gate-Source Cut-Off Voltage	V _{gs(off)}	I _d =1mA, V _{ds} =10V	0.5	-	1.2	V
Drain-Source On-State Resistance *	R _{ds(on)}	I _d =3A, V _{gs} =4.5V	-	0.026	0.035	Ω
		I _d =3A, V _{gs} =2.5V	-	0.035	0.048	Ω
Forward Transfer Admittance *	Y _{fs}	I _d =4A, V _{ds} =10V	-	14	-	S
Body Drain Diode Forward Voltage	V _f	I _f =6A, V _{gs} =0V	-	0.85	1.1	V

* Effective during pulse test.

Dynamic Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	C _{iss}	V _{ds} =10V, V _{gs} =0V f=1MHz	-	760	-	pF
Output Capacitance	C _{oss}		-	430	-	pF
Feedback Capacitance	C _{rss}		-	200	-	pF

Switching Characteristics

Ta = 25°C

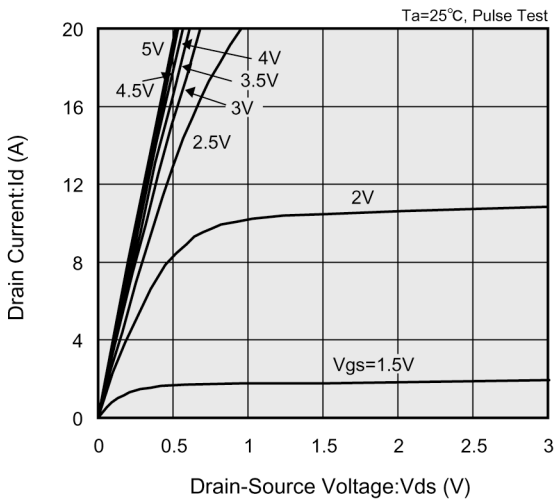
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	t _{d(on)}	V _{gs} =5V, I _d =3A V _{dd} =10V	-	10	-	ns
Rise Time	t _r		-	20	-	ns
Turn-Off Delay Time	t _{d(off)}		-	55	-	ns
Fall Time	t _f		-	15	-	ns

Thermal Characteristics

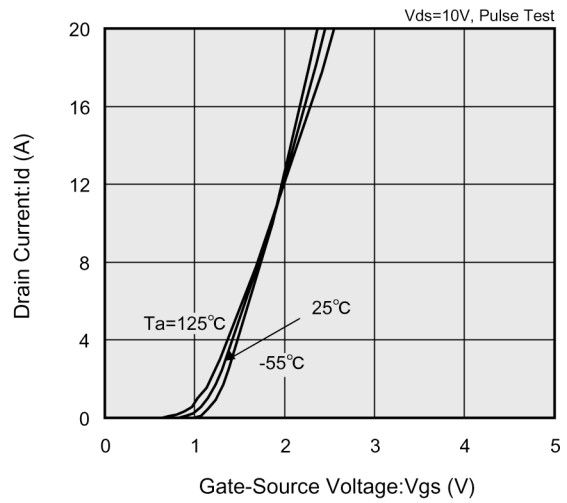
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	R _{th(ch-a)}	Implement on a glass epoxy resin PCB	-	62.5	-	°C/W

TYPICAL PERFORMANCE CHARACTERISTICS

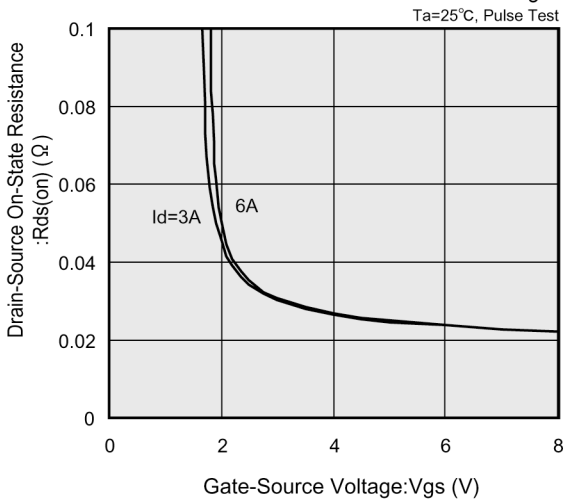
(1) Drain Current vs. Drain-Source Voltage



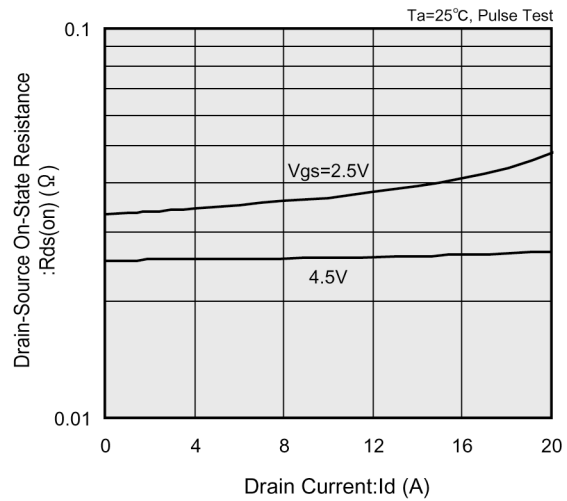
(2) Drain Current vs. Gate-Source Voltage



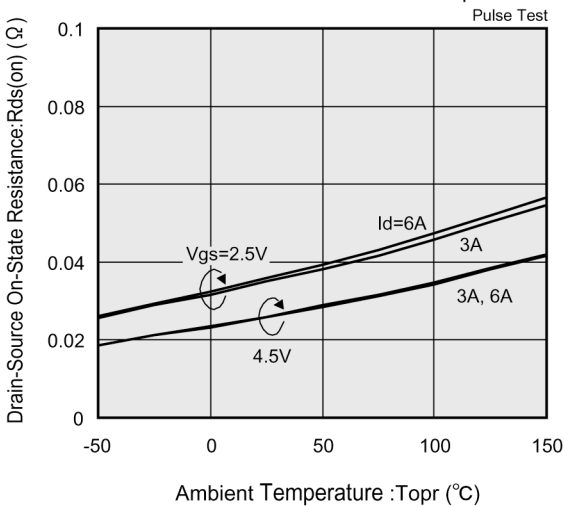
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



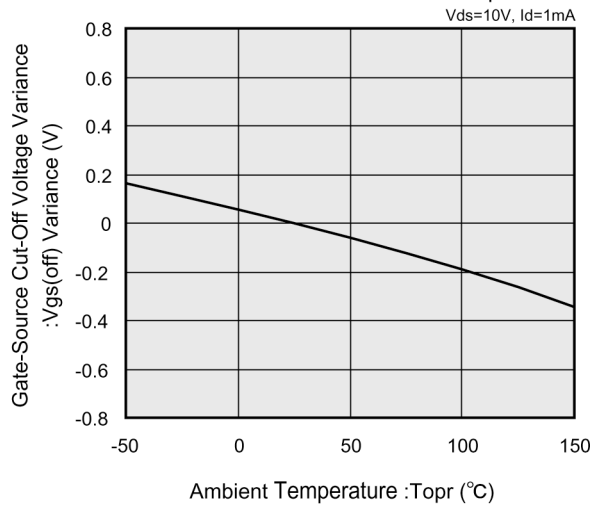
(4) Drain-Source On-State Resistance vs. Drain Current



(5) Drain-Source On-State Resistance vs. Ambient Temperature

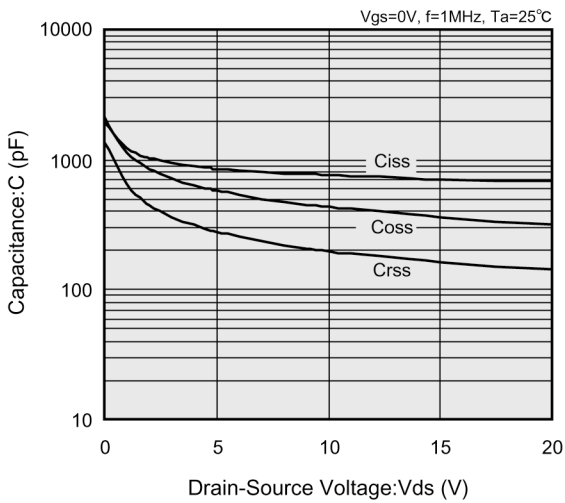


(6) Gate-Source Cut-Off Voltage Variance vs. Ambient Temperature

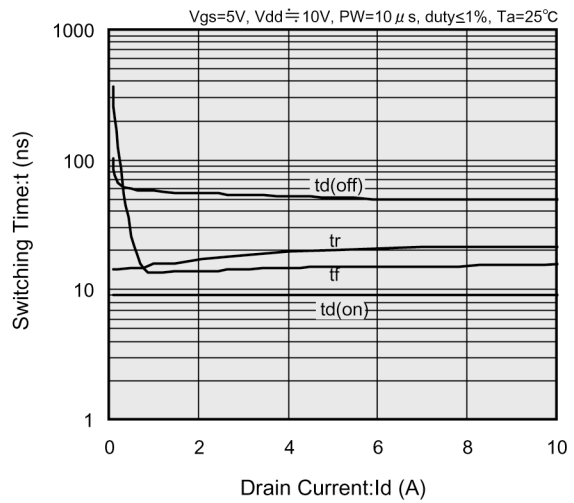


TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

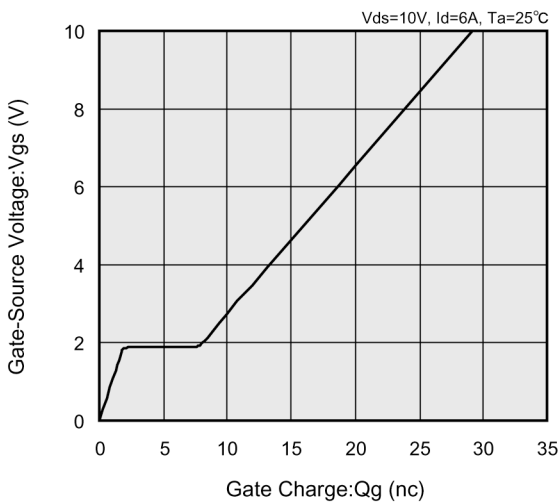
(7) Capacitance vs. Drain-Source Voltage



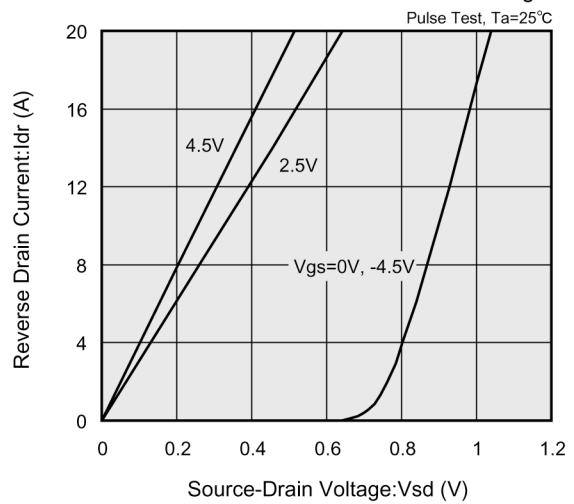
(8) Switching Time vs. Drain Current



(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current vs. Source-Drain Voltage



(11) Standardized transition Thermal Resistance vs. Pulse Width

